



PBHV9560Z

600 V, 0.5 A PNP high-voltage low V_{CEsat} (BISS) transistor

12 August 2014

Product data sheet

1. General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8560Z

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C
- High collector current gain h_{FE} at high I_C
- AEC-Q101 qualified

3. Applications

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- HID front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-600	V
I _C	collector current		-	-	-0.5	A
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -50 mA; T _{amb} = 25 °C	70	130	-	

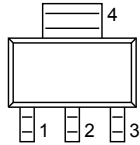
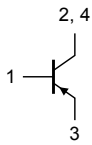


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 <p>SC-73 (SOT223)</p>	 <p><i>sym028</i></p>
2	C	collector		
3	E	emitter		
4	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV9560Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9560Z	HV956Z

8. Limiting values

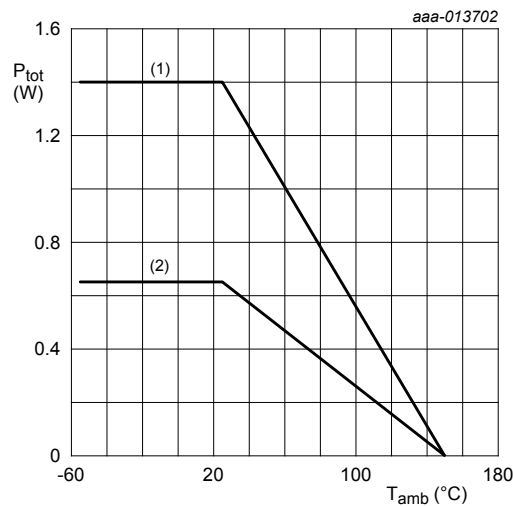
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-600	V
V _{CEO}	collector-emitter voltage	open base		-	-600	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-600	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-0.5	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1.4	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



(1) FR4 PCB, mounting pad for collector 6 cm²
 (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	190	K/W
			[2]	-	-	89	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

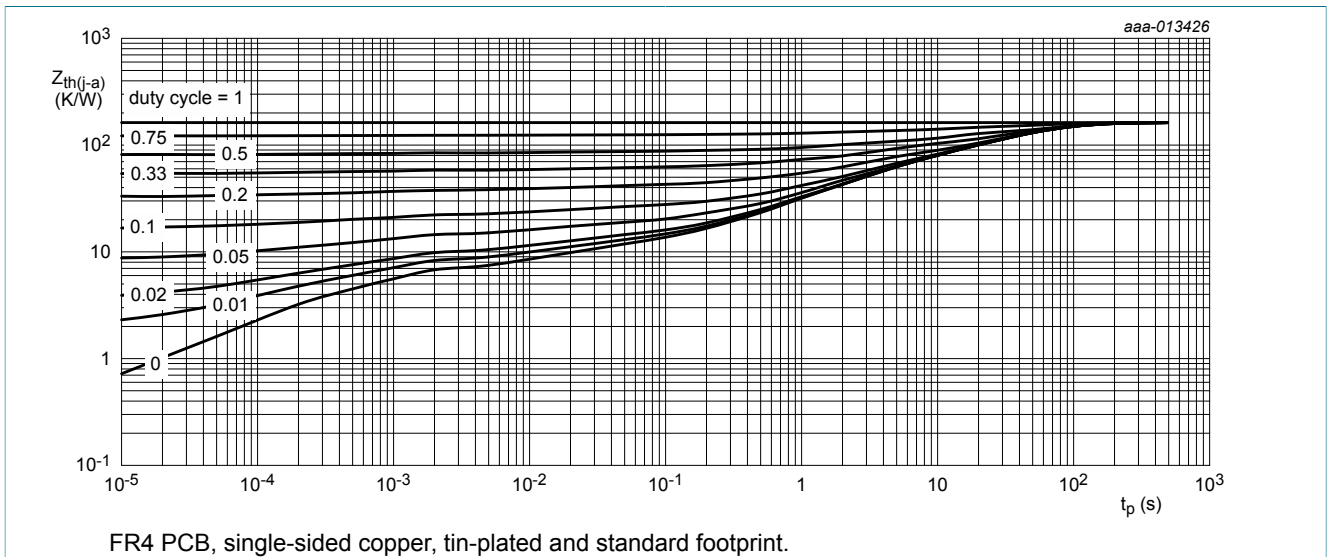


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

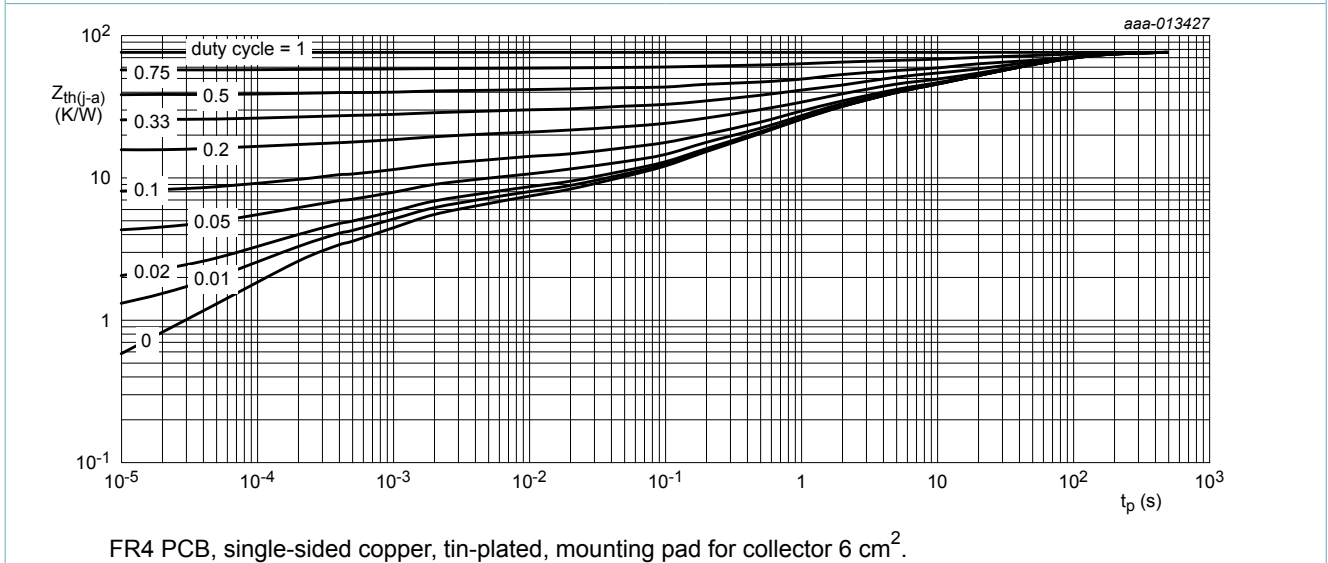
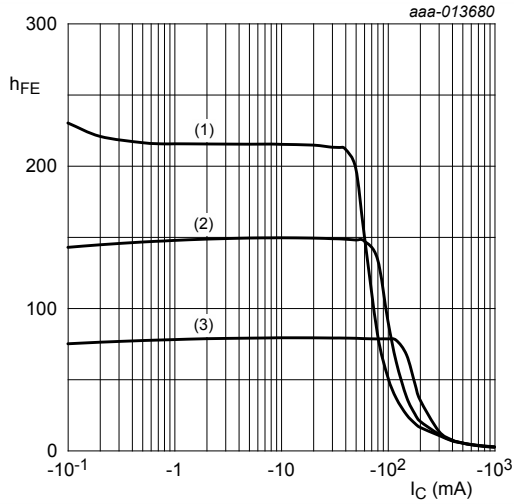


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

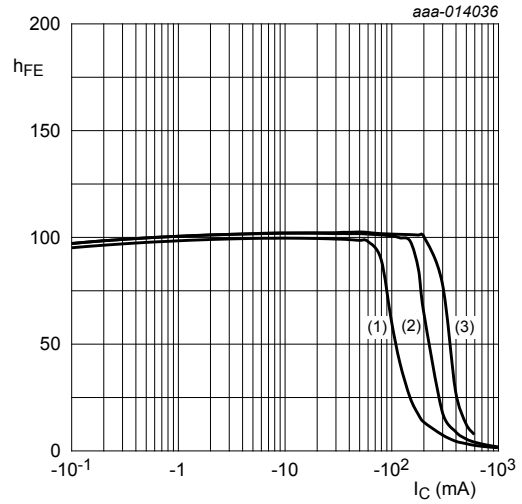
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = -400 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
		V _{CB} = -400 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -400 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -50 mA; T _{amb} = 25 °C	70	130	-	
		V _{CE} = -10 V; I _C = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	50	90	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -50 mA; I _B = -5 mA; T _{amb} = 25 °C	-	-150	-250	mV
		I _C = -100 mA; I _B = -20 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-140	-250	mV
V _{BEsat}	base-emitter saturation voltage	I _C = -50 mA; I _B = -5 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-900	mV
f _T	transition frequency	V _{CE} = -10 V; I _C = -30 mA; f = 100 MHz	-	38	-	MHz
C _c	collector capacitance	V _{CB} = -20 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	12	-	pF
C _e	emitter capacitance	V _{EB} = -0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	390	-	pF



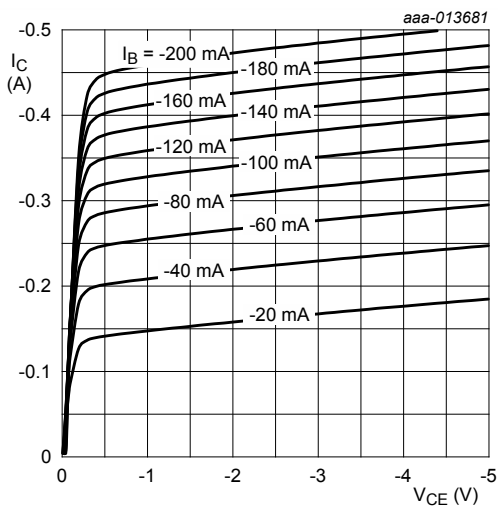
$V_{CE} = -10\text{ V}$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 4. DC current gain as a function of collector current; typical values



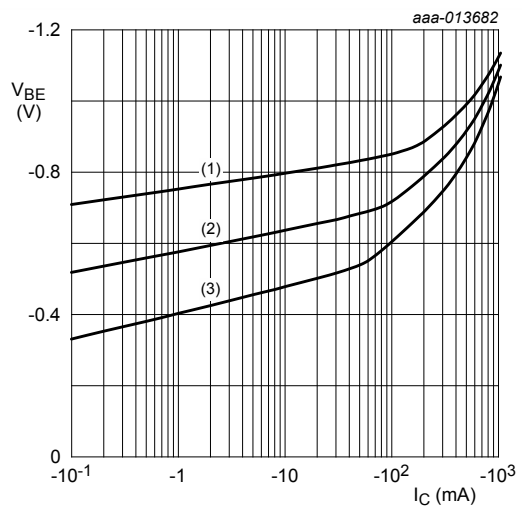
$h_{FE} = f(I_C)$
 $T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $V_{CE} = -10\text{ V}$
 (2) $V_{CE} = -25\text{ V}$
 (3) $V_{CE} = -50\text{ V}$

Fig. 5. DC current gain as a function of collector current; typical values



$T_{amb} = 25\text{ }^\circ\text{C}$

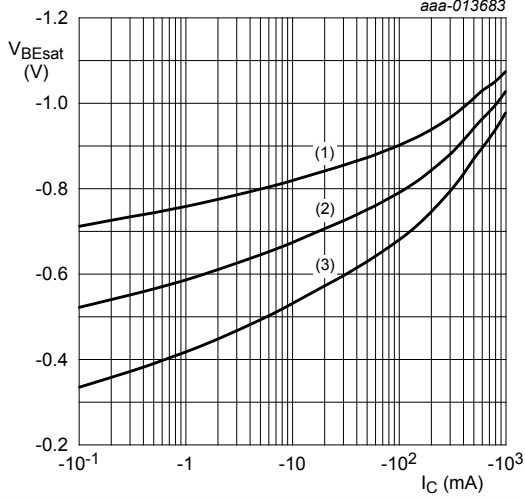
Fig. 6. Collector current as a function of collector-emitter voltage; typical values



$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

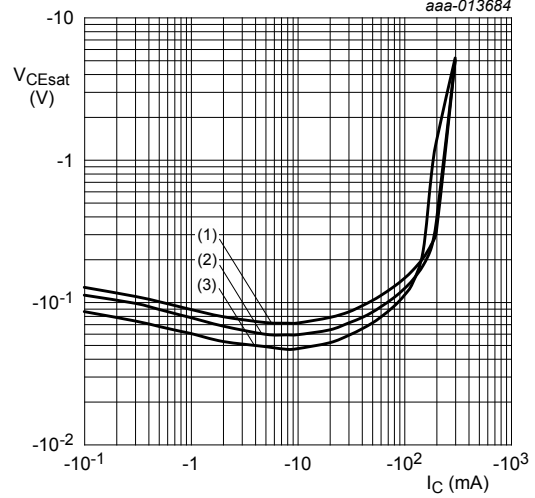
Fig. 7. Base-emitter voltage as a function of collector current; typical values

600 V, 0.5 A PNP high-voltage low VCEsat (BISS) transistor



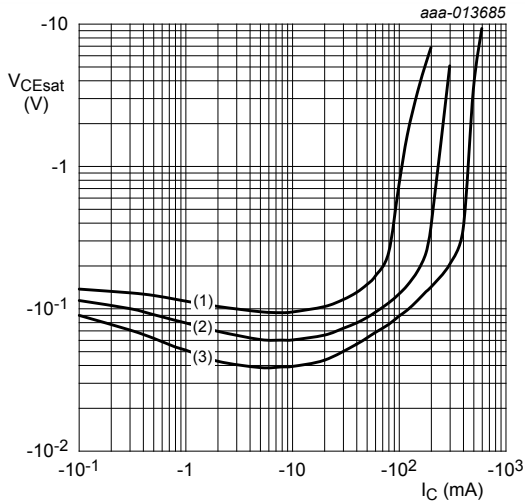
$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values



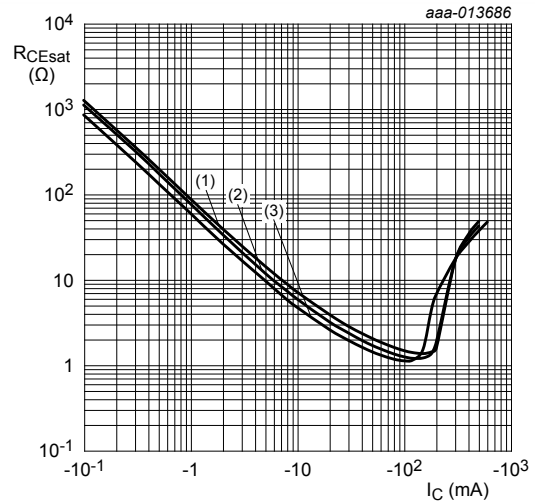
$I_C/I_B = 5$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



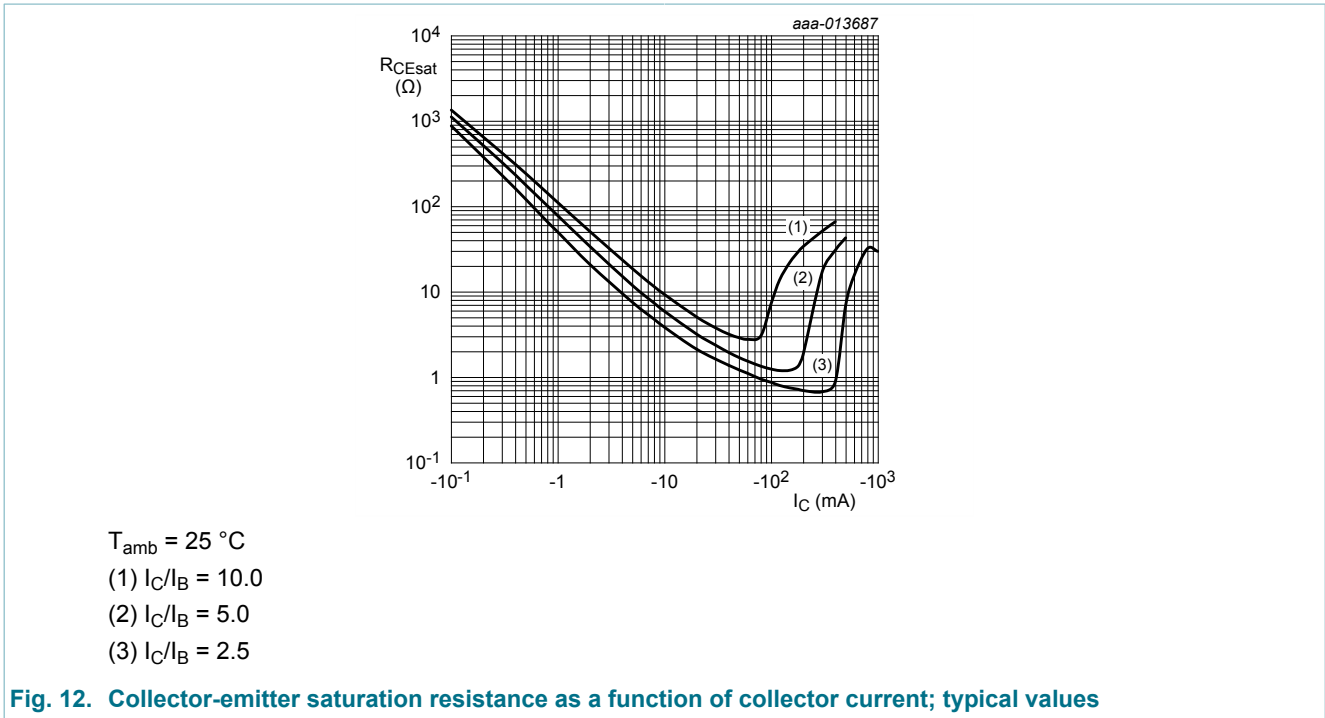
$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 10.0$
 (2) $I_C/I_B = 5.0$
 (3) $I_C/I_B = 2.5$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 5$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values



11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

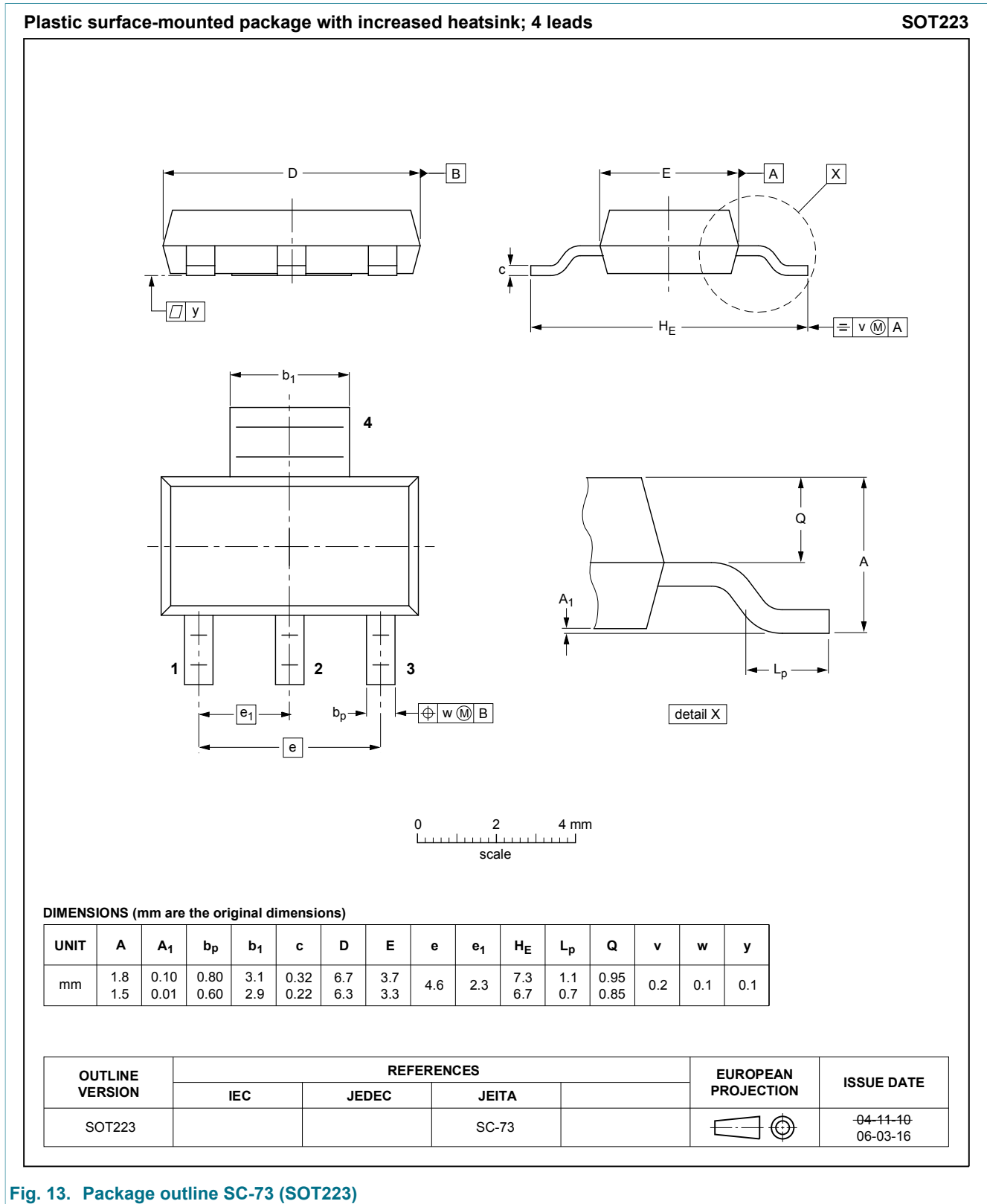


Fig. 13. Package outline SC-73 (SOT223)

13. Soldering

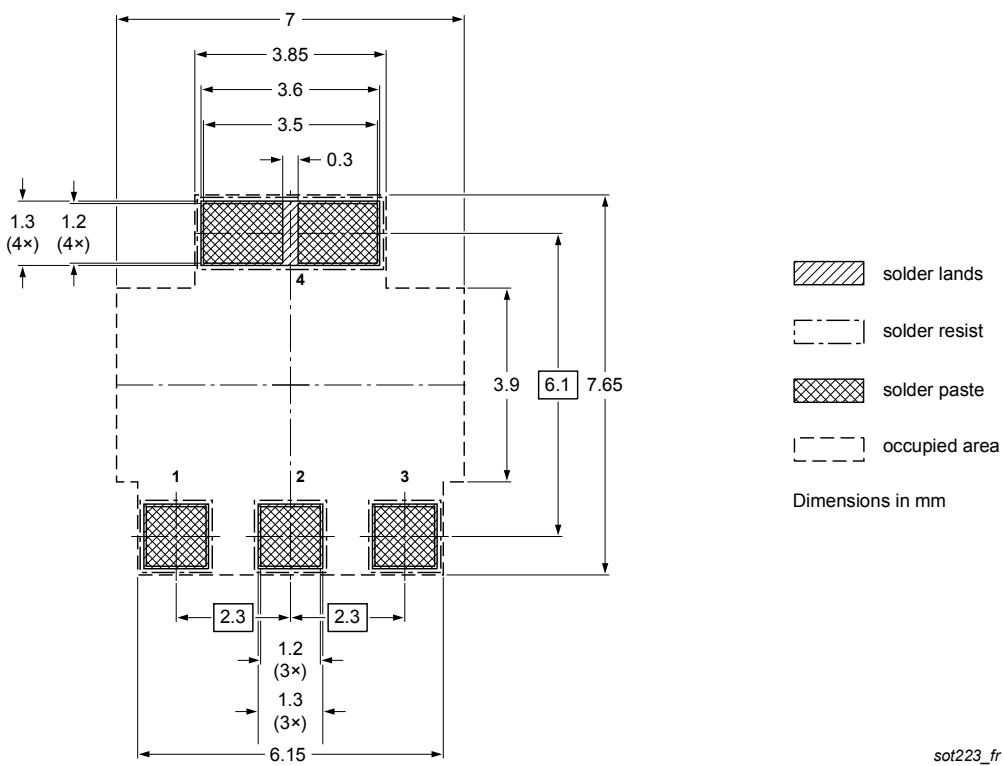


Fig. 14. Reflow soldering footprint for SC-73 (SOT223)

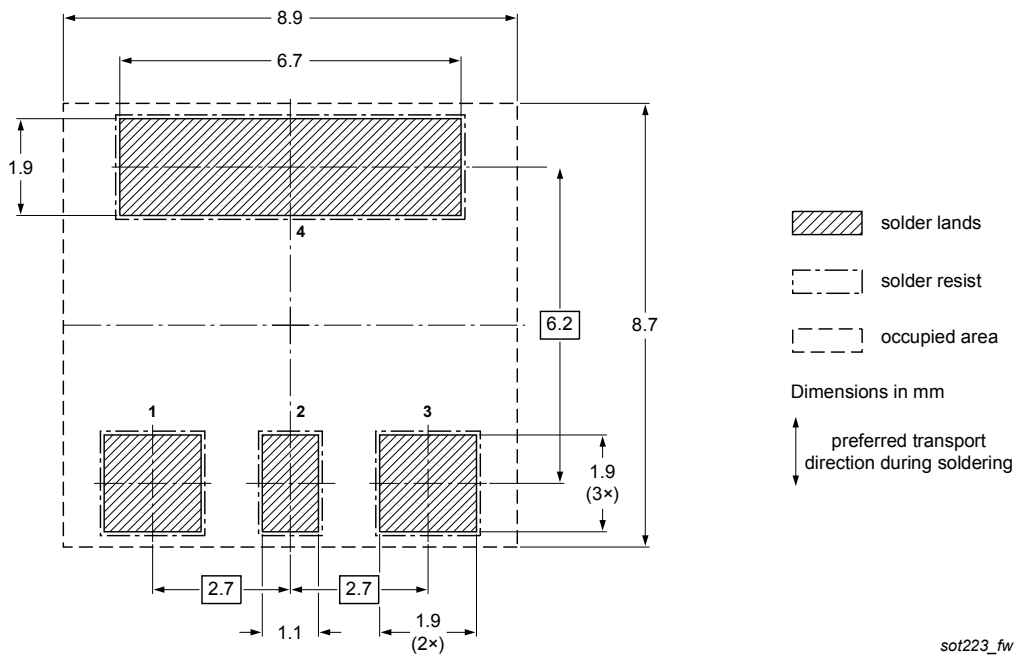


Fig. 15. Wave soldering footprint for SC-73 (SOT223)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9560Z v.1	20140812	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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